PTO-1449

Information Disclosure Citation In an Application

Application No	Applicant(s)
09/736,043	Yue (mni) Kuo
Docket Number	**Group Art Unit**	**Filing Date**
017575.0414 (TAMUS 1529)	2823	12/12/2000

U.S. PATENT DOCUMENTS

	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
A						
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FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
C	"Control Using Cl_2 Gas as a Single Reactant," J. Vac. Sci. Technol. B, 15 (2), p. 237	1997
D	"National Technology Roadmap for Semiconductors (NTRS)," Semiconductor Industry Association (SIA)	1997
E	H. Miyazaki, et al., "Copper Dry Etching with Precise Wafer-temperature Control Using Cl_2 Gas as a Single Reactant," J. Vac. Sci. Technol. B, 15 (2), p. 237	1997
F	J.W. Lee, et al., "Copper Dry Etching with Cl_2 Ar Plasma Chemistry," J. Electrochem. Soc., 145 (7), p. 2585	1998
G	Y. Ohshita, et al., "Lower Temperature Plasma Etching of Cu Using IR Light Irradiation," Thin Solid Films, 262, p. 67	1995
H	G.C. Schwartz, et al., "Reactive Ion Etching of Copper Films," J. Electrochem. Soc., 130, p. 1777	1983
I	B.J. Howard, et al., "Reactive Ion Etching of Copper in SiC14-based Plasmas," Appl. Phys. Lett., 59, p. 914	1991
J	M. Markert, et al., "Copper Dry Etching Technique for ULSI Interconnections," Microelectronic Engineering, 35, p. 333	1997
K	IBM Journal of Research and Development, special issue on Plasma Processing, Guest editor, Y. Kuo, 43(1/2)	1999
L	Sangheon Lee, et al., "Process Study of a New Copper Dry Etching Method – The HCL Chemistry," Elecrochem. Soc. Plasma Processing XIII Proceedings	2000
M	Sangyu Lee, et al., "Amorphous Silicon Thin Film Transistor Fabricated with a New Copper Dry Etching Method," Procs. ECS TFTTV Symp., Phoenix AZ, pp. 34-39	2001
N	Sangheon Lee, et al., "A Reactive Ion Etching Based Copper Etch Process" Thin Film Microelectronics Lab., TAMU, presented on 11/02/99, Dallas, Texas	1999
O	Yue Kuo, et al., "A Reactive Ion Etching Based Copper Etch Process," AiChE's 1999 Annual Meeting, Reasearch & Development for Results, www.aiche.org	1999
P	Yue Kuo, et al., " Amorphous Silicon Thin-Film Transistors Fabricated with a New Copper Etching Method," Meeting Abstracts of the Electrochemical Society, Abstract No. 762	2000
Q	Yue Kuo, et al., "A Novel Plasma-Based Copper Dry Etching Method," Jpn. J. Appl. Phys., Vol. 39, pp. L188-L190	03/15/2000
R	Yue Kuo, et al., "A New Copper Reactive Ion Etching Process," Meeting Abstracts, The 1999 Joint International Meeting, Volume 99-2, Abstract No. 704, Presented October 20, 1999	1999
S	Yue Kuo, et al., "Plasma Process of a New Copper Dry Etching Method," Meeting Abstracts, Toronto, The Electrochemical Society, Volume 2000-1, Abstract No. 296	2000
T	Yue Kuo, et al., "A New Copper Dry Etching Process," The Electrochemical Society, Inc., Proceedings Volume 99-30, pp. 328-335	
U	Yue Kuo, et al., "[190i] – A Reactive Ion Etching Based Copper Etch Process," American Institute of Chemical Engineers, www.aiche.org conferences techpro...aperdetail.asp?PaperID=3270&DSN=annual99	1999

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	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
D	Yue Kuo, et al., "A Novel Room-Temperature Plasma-Based Copper Etching Process for VLSI," Paper #2.D Presented in 2000 VLSI Multilevel Inteconnection Conference (VMIC), Santa Clara, California	06 27 2000
E	Brian Chapman, "Glow Discharge Processes – Sputtering and Plasma Etching", p. 314	1980
F	Brian Chapman, "Glow Discharge Processes – Sputtering and Plasma Etching", p. 317	1980
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